

## N-Channel Enhancement-Mode

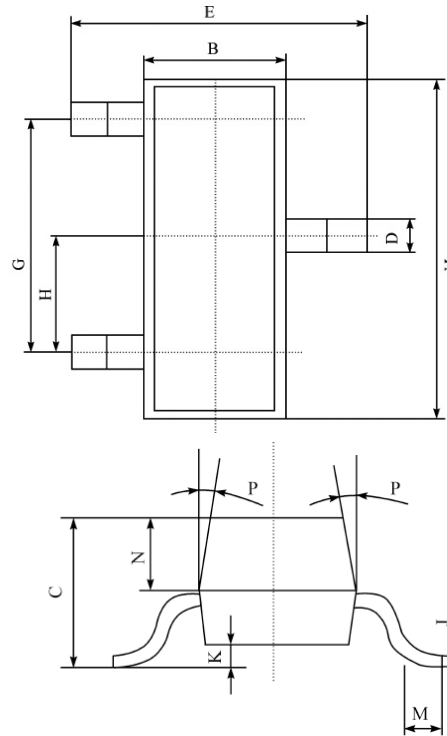
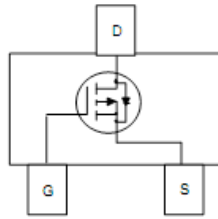
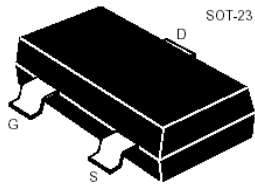
## MOSFETs

**BW3402**

### MECHANICAL DATA

\* Case: SOT-23 Molded plastic

\* Epoxy: UL94V-O rate flame retardant



A	2.90±0.10
B	1.30±0.10
C	1.00±0.10
D	0.40±0.10
E	2.40±0.20
G	1.90±0.10
H	0.95±0.05
J	0.13±0.05
K	0.00-0.10
M	≥0.2
N	0.60±0.10
P	7±2°

Dimensions in millimeter

### Maximum Ratings (Tc=25°C unless otherwise noted)

Parameter	Symbol	BW3402	Unit
Drain-Source Voltage	BVDSS	30	V
Gate- Source Voltage	VGS	12	V
Drain Current (continuous)	ID	4.6	A
Drain Current (pulsed)	IDM	16	A
Total Device Dissipation	PD	1380	mW
Junction	TJ	150	°C
Storage Temperature	Tstg	-55to+150	°C

**Maximum Ratings** (Tc=25°C unless otherwise noted)

Parameter	Symbol	MIN	TYP	MAX	Unit
Drain-Source Breakdown Voltage (ID =250uA,VGS=0V)	BVDSS	30		--	V
Gate Threshold Voltage (ID = 250uA,VGS= VDS)	VGS(th)	0.7		1.8	V
Diode Forward Voltage Drop (IS= 1A,VGS=0V)	VSD	--		1	V
Zero Gate Voltage Drain Current (VGS=0V, VDS= 24V) (VGS=0V, VDS= 24V, TA=55°C)	IDSS	--		1 5	uA
Gate Body Leakage (VGS=+12V, VDS=0V)	IGSS	--		+/- 100	nA
Static Drain-Source On-State Resistance (ID= 4.6A,VGS=10V)	RDS(ON)	--		30	mΩ
Static Drain-Source On-State Resistance (ID= 4A,VGS=4.5V)		--		50	mΩ
Static Drain-Source On-State Resistance (ID= 1A,VGS= 2.5V)				100	mΩ
Input Capacitance (VGS=0V, VDS= 15V,f=1MHz)	CISS		954	--	pF
Output Capacitance (VGS=0V, VDS= 15V,f=1MHz)	COSS		115	--	pF
Turn-ON Time (VDS= 15V, VGS= 10V, RGEN=6Ω)	t(on)		6.3	--	ns
Turn-OFF Time (VDS= 15V, VGS= 10V, RGEN=6Ω)	t(off)	--	38.2	--	ns

Pulse Width&lt;300μs; Duty Cycle&lt;2.0%